# MSKSEMI 美森科













**ESD** 

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MOV

OT PL

# MSAD8605 / MSAD8606 / MSAD8608

**Product specification** 





#### **GENERAL DESCRIPTION**

The MSAD860x families of products offer low voltage o peration and rail-to-rail input and output, as well as exc ellent speed/power consumption ratio, providing an exce llent bandwidth (8MHz), a slew rate of 6.5V/us, and a quiescent current of 510uA/amplifier at 5V. The op-amp s are unity gain stable and feature an ultra-low input bi as current.

The MSAD860x are designed to provide optimal performance in low-voltage systems. They offset voltage are 2.5mV for the provide rail-to-rail I/O, and the maximum input devices. Their capacitive load capability is also go od at low supply voltages. The operating range is from 2.2 V to 5.5 V.

The MSAD860x families of operational amplifiers are sp ecified at the full temperature range of -40°C to +85°C under single or dual power supplies of 2.2V to 5.5V.

## **FEATURES**

- Input Offset Voltage: 2.5mV (MAX)
- Supply Current: 510μA/ch
- Supply Range: 2.2V to 5.5V
- Gain Bandwidth: 8MHz
- Slew rate: 6.5V/µs
- Rail-to-Rail Input and Output
- Micro size Packages:
- MSAD8605ARTZ-REEL7: SOT-23-5
- MSAD8606ARZ: SOP-8
- MSAD8608ARZ-REEL7: SOP-14

## **Applications**

- Photodiode Amplification
- Active Filter and Buffer
- Battery Powered Electronics
- Sensors
- Cellular and Cordless Phones
- Test Equipment
- Driving A/D Converters

## **Reference News**

Type No	SOT-23-5	MARKING
MSAD8605ARTZ-REEL7		ВЗА

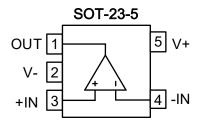
Type No	SOP-8	MARKING
MSAD8606ARZ		MSKSEMI 8606ARZ ● MS**

Type No	SOP-14	MARKING
MSAD8608ARZ-REEL7	A LEISEN	MSKSEMI 8608ARZ ● MS**



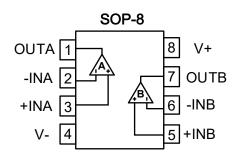
# Pin Configuration and Functions (Top View)

# **Pin Description**



F	PIN		
NAME	Number	I/O	DESCRIPTION
+IN	3	I	Positive (noninverting) input
-IN	4	I	Negative (inverting) input
NC	-	-	No Connection
OUT	1	0	Output
V+	5		Positive (highest) power
VŤ	5	-	supply
V-	2		Negative (lowest) power
V-	2	-	supply

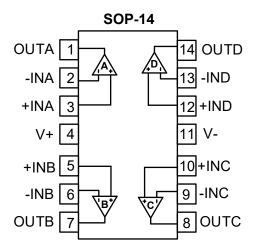
## **Pin Description**



PII	N	I/O	DESCRIPTION		
NAME	Number	.,0	DESCRIPTION		
+INA	3	I	Noninverting input, channel A		
+INB	5	I	Noninverting input, channel B		
-INA	2	I	Inverting input, channel A		
-INB	6	I	Inverting input, channel B		
OUTA	1	0	Output, channel A		
OUTB	7	0	Output, channel B		
V-	4	-	Negative (lowest) power supply		
V+	8	-	Positive (highest) power supply		



# **Pin Description**



PII	N	I/O	DESCRIPTION			
NAME	Number	.,0	DESCRIPTION			
+INA	3	I	Noninverting input, channel A			
+INB	5	I	Noninverting input, channel B			
+INC	10	I	Noninverting input, channel C			
+IND	12	I	Noninverting input, channel D			
-INA	2	I	Inverting input, channel A			
-INB	6	I	Inverting input, channel B			
-INC	9	I	Inverting input, channel C			
-IND	13	I	Inverting input, channel D			
OUTA	1	0	Output, channel A			
OUTB	7	0	Output, channel B			
OUTC	8	0	Output, channel C			
OUTD	14	0	Output, channel D			
V-	4	-	Negative (lowest) power supply			
V+	11	-	Positive (highest) power supply			



# **TYPICAL APPLICATION**

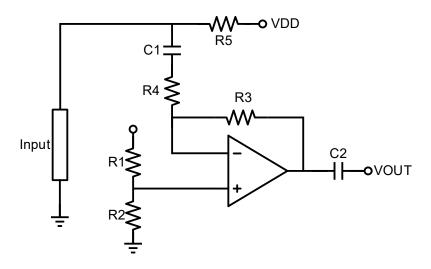


Figure 1. Typical Application

# **ORDER INFORMATION**

P/N	PKG	QTY
MSAD8605ARTZ-REEL7	SOT-23-5	3000
MSAD8606ARZ	SOP-8	2500
MSAD8608ARZ-REEL7	SOP-14	2500



#### **SPECIFICATIONS**

## Absolute Maximum Ratings(1)

		MIN	MAX	UNIT
	Supply Voltage		6	V
Voltage	Signal Input Terminals Voltage <sup>(2)</sup>	(V-) - 0.5	(V+) + 0.5	V
	Signal Input Terminals Voltage <sup>(3)</sup>	(V-) - 0.5	(V+) + 0.5	V
	Signal Input Terminals Current <sup>(2)</sup>	-10	10	mA
Current	Signal output Terminals Current <sup>(3)</sup>	-200	200	mA
	Output Short-Circuit <sup>(4)</sup>	Cont	inuous	
	Operating Temperature Range	-40	85	°C
$\theta_{JA}$	Storage Temperature Range	-65	150	°C
	Junction Temperature	-40	150	°C

- (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
- (2) Input terminals are diode clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails should be current limited to 10mA or less.
- (3) Output terminals are diode-clamped to the power-supply rails. Output signals that can swing more than 0.5V beyond the supply rails should be current-limited to ±200mA or less.
- (4) Short-circuit to ground, one amplifier per package.

# **ESD Ratings**

			VALUE	UNIT
	Human-Body Model (HBM)	±2000	<b>V</b>	
$V_{(ESD)}$	Electrostatic discharge	Charged-Device Model (CDM)	±500	<b>V</b>
		Machine Model	100	<b>V</b>

# **Recommended Operating Conditions**

		MIN	MAX	UNIT
Supply voltage,	Single-supply	2.2	5.5	V
Vs= (V+) - (V-)	Dual-supply	±1.1	±2.75	V



# **ELECTRICAL CHARACTERISTICS (V<sub>S</sub> = +5V)**

At  $T_A = 25$ °C,  $V_{IN}=V_{OUT}=V_S$  /2, unless otherwise noted.

	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET \	<b>VOLTAGE</b>			•	•	
Vos	Input Offset Voltage		-2.5	0.8	2.5	mV
dV <sub>OS</sub> /dT	Input Offset Voltage Average Drift	T <sub>A</sub> = -40°C to 85°C		0.6		μV/°C
INPUT CL	JRRENT					
I <sub>B</sub>	Input Bias Current			10		pA
los	Input Offset Current			5		pА
NOISE						
V <sub>N</sub>	Input Voltage Noise	f=0.1Hz to 10Hz		4		$\mu V_{PP}$
<b>e</b> n	Input Voltage Noise PSD	f=1kHz		8		nV/√Hz
INPUT VC	DLTAGE					
V <sub>CM</sub>	Common-Mode Voltage Range		$V_{S-}$		V <sub>S+</sub> +0.1	V
CMRR	Common-Mode Rejection Ratio	V <sub>CM</sub> =0.1V to 4V	85	95		dB
FREQUE	NCY RESPONSE					
GBW	Gain-Bandwidth Product			8		MHz
SR	Slew Rate	G = +1, V <sub>IN</sub> =2V Step		6		V/µs
ts	Settling Time	G = +1, V <sub>IN</sub> =2V Step		0.6		μs
OUTPUT						
Av	Open-Loop Voltage Gain	V <sub>OUT</sub> =0.5V to 4.8V	95	105		dB
V <sub>OH</sub>	High output voltage swing	R <sub>L</sub> =10kΩ			5	mV
$V_{OL}$	Low output voltage swing	R <sub>L</sub> =10kΩ			5	mV
	Output Short-Circuit	Source Current		26		mA
I <sub>SC</sub>	Current	Sink <u>C</u> urrent		50		mA
C <sub>L</sub> <sup>(1)</sup>	Capacitive Load Drive	=0.2V Step V <sub>IN</sub>			1000	pF



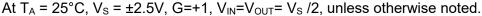
# MSAD8605 / MSAD8606 / MSAD8608

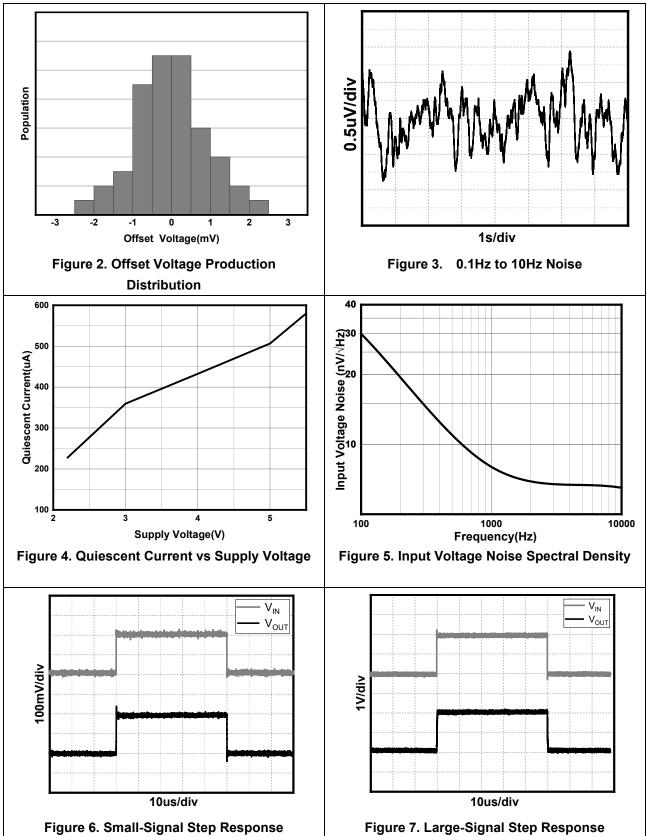
POWER SUPPLY						
PSRR	Power-Supply Rejection Ratio	V <sub>S</sub> =2.5V to 5.5V	90	100		dB
Vs	Operating Voltage Range	I <sub>O</sub> =0A	2.2		5.5	<b>&gt;</b>
ΙQ	Quiescent Current/Amplifier	I <sub>O</sub> =0A		510	600	μΑ

<sup>(1)</sup> Capacitive load drive means that above a given maximum value, the output waveform will oscillate under the step response.



## TYPICAL CHARACTERISTICS







## **Detailed Description**

## Overview

Th MSAD860x devices are a high-bandwidth, unity-gain stable, rail-to-rail operational amplifier available in single and dual-channel versions that operate in a single-supply voltage range of 2.2V to 5.5V(±1.1V to ±2.75V). A high supply voltage of 6V(absolute maximum) can permanently damage the amplifier. Rail-to-rail input and output wobbles significantly increase the dynamic range, especially in low-supply applications. Good layout practices require that a 0.1uF capacitor be used where it is tightly threaded through the power supply pin.

#### **Phase Reversal Protection**

The MSAD860x devices have internal phase-reversal protection. Many op amps exhibit phase reversal when the input is driven beyond the linear common-mode range. This condition is most often encountered in noninverting circuits when the input is driven beyond the specified common-mode voltage range, causing the output to reverse into the opposite rail. The input of the AD860x prevents phase reversal with excessive commonmode voltage. Instead, the appropriate rail limits the output voltage.

## **Typical Applications**

### 1 Voltage Follower

As shown in Figure 8, the voltage gain is 1. With this circuit, the output voltage  $V_{\text{OUT}}$  is configured to be equal to the input voltage  $V_{\text{IN}}$ . Due to the high input impedance and low output impedance, the circuit can also stabilize the output voltage, the output voltage expression is

$$V_{OUT} = V_{IN} \tag{1}$$

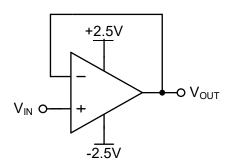


Figure 8. Voltage Follower

### 2 Inverting Proportional Amplifier

As shown in Figure 9, for a reverse-phase proportional amplifier, the input voltage  $V_{\text{IN}}$  is amplified by a voltage gain that depends on the ratio of R1 to R2. The output voltage  $V_{\text{OUT}}$  is inversely with the input voltage  $V_{\text{IN}}$ . The input impedance of the circuit is equal to R1, and the output voltage expression is

$$V_{OUT} = \frac{R2}{R1} V_{IN}$$
 (2)



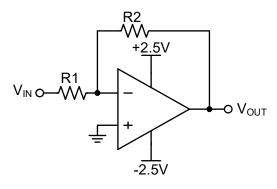


Figure 9. Inverting Proportional Amplifier

## 3 Noninverting Proportional Amplifier

As shown in Figure 10, for a noninverting amplifier, the input voltage  $V_{\text{IN}}$  is amplified by a voltage gain that depends on the ratio of R1 to R2. The output voltage  $V_{\text{OUT}}$  is in phase with the input voltage  $V_{\text{IN}}$ . In fact, this circuit has a high input impedance because its input side is the same as the input side of the operational amplifier. The output voltage expression is

$$V_{OUT} = (1 + \frac{R2}{R1})V_{IN}$$
 (3)

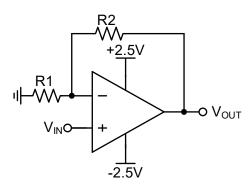


Figure 10. Noninverting Proportional Amplifier

# **Layout Guidelines**

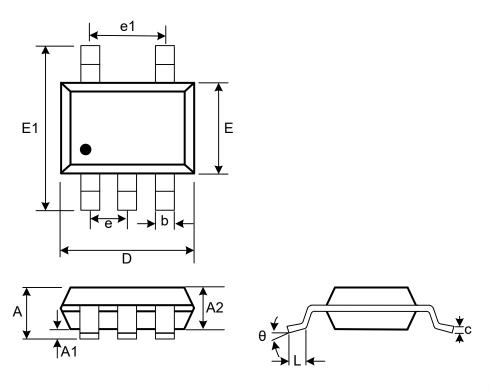
Attention to good layout practices is always recommended. Keep traces short. When possible, use a PCB ground plane with surface-mount components placed as close to the device pins as possible. Place a 0.1uF capacitor closely across the supply pins.

These guidelines should be applied throughout the analog circuit to improve performance and provide benefits such as reducing the EMI susceptibility.



# **PACKAGE DESCRIPTION**

## SOT23-5

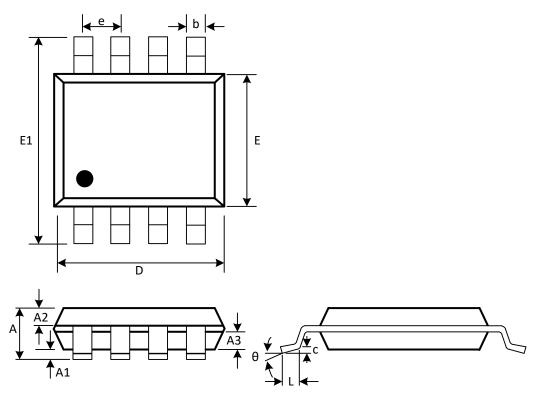


(Unit: mm)

Symbol	Min	Max
A	1.05	1.25
A1	0	0.1
A2	1.05	1.15
b	0.3	0.5
С	0.1	0.2
D	2.82	3.02
е	0.95(BSC)	
e1	1.9(BSC)	
E	1.5	1.7
E1	2.65	2.95
L	0.3	0.6
θ	0°	8°



SOP-8

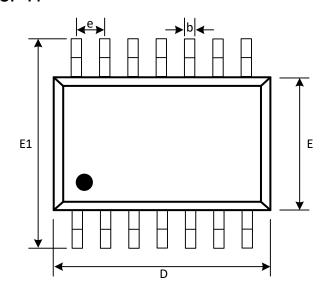


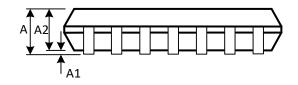
(Unit: mm)

Symbol	Min	Max
А	1.300	1.600
A1	0.050	0.200
A2	0.550	0.650
A3	0.550	0.650
b	0.356	0.456
С	0.203	0.233
D	4.800	5.000
е	1.270(BSC)	
E	3.800	4.000
E1	5.800	6.200
L	0.400	0.800
θ	0°	8°



**SOP-14** 







(Unit: mm)

Symbol	Min	Max
А	1.350	1.750
A1	0.100	0.250
A2	1.350	1.550
b	0.310	0.510
С	0.100	0.250
D	8.450	8.850
е	1.270(BSC)	
E1	5.800	6.200
E	3.800	4.000
L	0.400	1.270
θ	0°	8°



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